Reactive chemical vapour deposition (RCVD) of non-volatile terbium aromatic carboxylate thin films

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$T_1(\mathbf{K})$	P ₁ (Torr)	P ₀ (Torr)	P (Torr)
383.84	1.033	0.538	0.308
383.73	1.030	0.546	0.305
383.58	1.040	0.540	0.315
383.53	1.042	0.553	0.317
383.34	1.032	0.545	0.308
383.19	1.044	0.556	0.320
383.14	1.040	0.543	0.316
420.35	2.109	0.940	0.762
420.35	2.097	0.929	0.750
420.35	2.083	0.938	0.736
420.36	2.118	0.955	0.771
420.35	2.123	0.957	0.776
420.34	2.124	0.952	0.777
420.34	2.121	0.943	0.774
437.25	3.559	1.474	1.407
437.48	3.607	1.450	1.454
437.33	3.603	1.450	1.451
437.15	3.568	1.470	1.416
437.06	3.586	1.446	1.435
437.04	3.618	1.443	1.467
437.03	3.629	1.464	1.478

Table S1. The details of the vapor pressure measurements for Hpobz.

Three runs were carried out. The furnace was heated to a fixed temperature, and seven $T_1 - P_1$ readings were taken. The reaction cell was then cooled to the room temperature, and five $P_0 - T_0$ readings of the residual gas were taken. The vapor pressure P was derived as a difference $P=P_1 - P_0$. Experimental data are presented in the table.

Enthalpy and entropy of vaporization were determined by minimization of the sum $\sum (P_{exp} - P_{calc})^2$ according to the equation $R \ln P = \Delta S - \Delta H / T$ to be $\Delta H (416 K) = 12654 \pm 282 \, cal \cdot mol^{-1}$ and $\Delta S = 16.48 \pm 0.65 \, cal \cdot mol^{-1} \cdot K^{-1}$. The calculation was performed at a confidence probability 0.95. The total standard deviation in pressure amounted to 0.045 Torr. The correlation coefficient between ΔH and ΔS was equal to -0.99904, *i.e.* the uncertainties in ΔH and ΔS given above are meaningless.



Figure S1. Curves of weight loss for Hbz and Hpobz under nitrogen atmosphere.



Figure S2. ¹H NMR (400 MHz, DMSO-d⁶) of Hbz and Hpobz (a) before and (b) after annealing at 300 °C during six hours ($p \sim 10^{-2}$ Torr; for clarity only aromatic region is shown).



Figure S3. IR spectra of (a) Tb(bz)₃ and (b) Tb(pobz)₃ (powder and thin films).



Figure S4. Raman spectra of (a) Tb(bz)₃ and (b) Tb(pobz)₃ (powder and thin films).



Figure S5. AFM images of $Tb(bz)_3(1)$ (Fig. 2(b)) annealed at 150 °C during: (a) 5 and (b) 30 minutes (10^{-2} Torr).



Figure S6. AFM images of Tb(bz)₃ thin film obtained at $T_3 = 250$ °C without (a) and with (b) further annealing at 150 °C during 30 minutes (10⁻² Torr).



Figure S7. (a) SEM and (b) AFM images of Tb(pobz)₃ thin film obtained at $T_3 = 250$ °C and further annealed at 150 °C during 30 minutes (10⁻² Torr).